

ABSTRACT OF THE DISCLOSURE

In a method of crystallizing a semiconductor film by introducing a metallic element that promotes crystallization, a gettering thereafter is effectively performed. A material film having a high tensile stress, typically a silicon nitride film, is formed in contact with the semiconductor film or heated after the formation thereof, thereby the metallic element in a crystalline semiconductor film is getterred to the material film having a high tensile stress. Thus, the metallic Interstitial silicon density element is removed or reduced to thereby form a getterred region.